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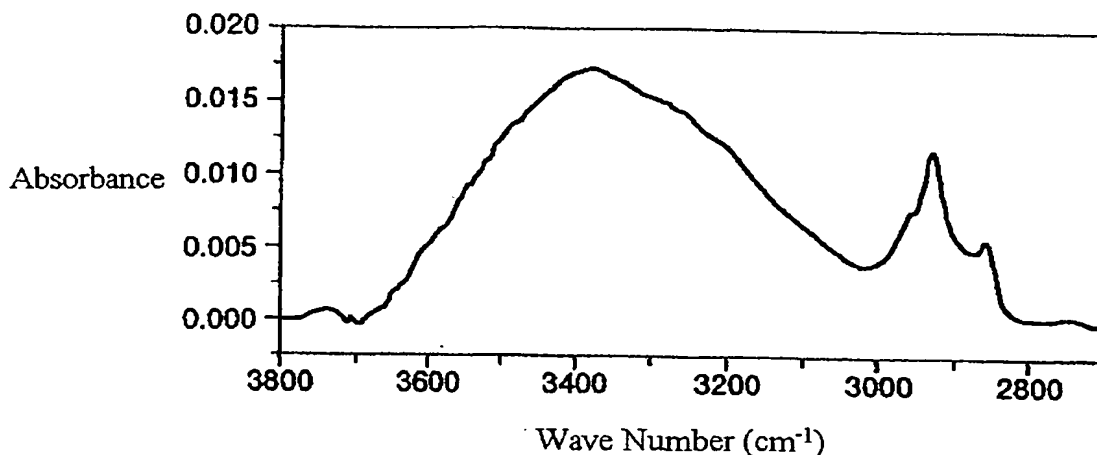
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(54) Title: SEMICONDUCTOR DEVICE, ELECTRONIC DEVICE AND ELECTRONIC APPARATUS

(Example 1)



(57) Abstract: An semiconductor device (1) of the invention includes a semiconductor substrate provided with a channel region (21), a source region (22) and a drain region (23), a gate insulating film (3) laminated on the channel region (21), and a gate electrode (5). The gate insulating film (3) is formed of an insulative inorganic material as a main material, and further contains hydrogen. The absorbance of infrared radiation of which wave number is in the range of 3200 to 3500 cm<sup>-1</sup> is 0.02 or less when the gate insulating film (3) to which an electric field has never been applied is measured with Fourier Transform Infrared Spectroscopy at room temperature.

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